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The invention relates to the nanostructured materials production technology, in particular to methods for producing nanostructures by electrochemical machining.

The method, according to the invention, comprises anodizing the surface of a GaAs wafer with (111)B crystallographic orientation in electrolyte. At the same time, the electrolyte comprises a 1M HNO₃ solution, and anodizing is carried out with the application of voltage in a range of 3...4 V for 10...30 min.

Claims: 1

Fig.: 2